

N-Channel Trench Power MOSFET

General Description

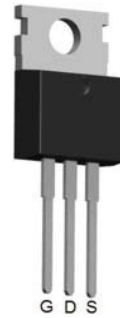
The HM1607 is N-channel MOS Field Effect Transistor designed for high current switching applications. Rugged EAS capability and ultra low $R_{DS(ON)}$ is suitable for PWM.

Features

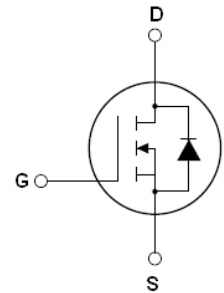
- $V_{DS}=75V$; $I_D=150A@V_{GS}=10V$;
 $R_{DS(ON)}<6.3m\Omega @V_{GS}=10V$
- Ultra Low On-Resistance
- High UIS and UIS 100% Test

Application

- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



To-220 Top View



Schematic Diagram

$$V_{DS} = 75V$$

$$I_D = 150A$$

$$R_{DS(ON)} = 5.0m\Omega$$

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM1607	HM1607	TO-220	-	-	-

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	75	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 25	V
$I_{D(DC)}$	Drain Current (DC) at $T_c=25^\circ C$	150	A
$I_{D(DC)}$	Drain Current (DC) at $T_c=100^\circ C$	115	A
$I_{DM(pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	600	A
P_D	Maximum Power Dissipation($T_c=25^\circ C$)	380	W
	Derating Factor	2.5	W/°C
EAS	Single Pulse Avalanche Energy (Note 2)	1000	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.EAS condition: $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
R_{JC}	Thermal Resistance, Junction-to-Case	0.4	$^{\circ}\text{C}/\text{W}$

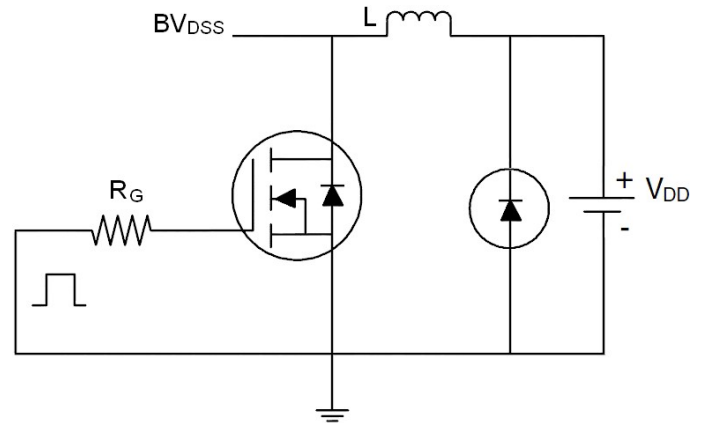
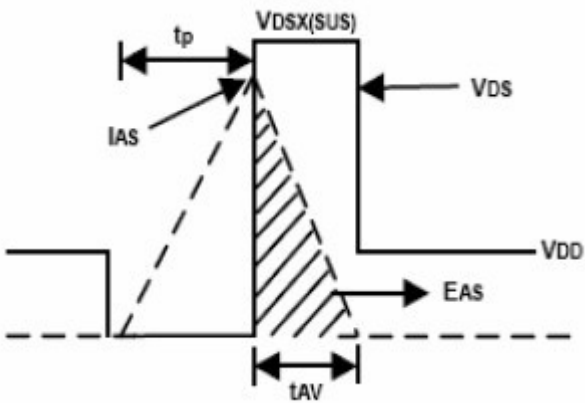
Table 3. Electrical Characteristics (TA=25 $^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	75			V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25 $^{\circ}\text{C}$)	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1	μA
I_{DSS}	Zero Gate Voltage Drain Current(Tc=125 $^{\circ}\text{C}$)	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2		4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10\text{V}, I_D=40\text{A}$		5.0	6.3	m Ω
Dynamic Characteristics						
g_{FS}	Forward Transconductance	$V_{DS}=50\text{V}, I_D=40\text{A}$	30			S
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		8184		PF
C_{oss}	Output Capacitance			955		PF
C_{riss}	Reverse Transfer Capacitance			463		PF
Q_g	Total Gate Charge	$V_{DS}=44\text{V}, I_D=40\text{A}$ $V_{GS}=10\text{V}$		158		nC
Q_{gs}	Gate-Source Charge			29		nC
Q_{gd}	Gate-Drain Charge			42		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=65\text{V}, I_D=40\text{A}, R_L=15\Omega$ $V_{GS}=10\text{V}, R_G=2.5\Omega$		25		nS
t_r	Turn-on Rise Time			29		nS
$t_{d(off)}$	Turn-Off Delay Time			53		nS
t_f	Turn-Off Fall Time			63		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)			150		A
I_{SDM}	Pulsed Source-Drain Current(Body Diode)			600		A
V_{SD}	Forward On Voltage ^(Note 1)	$T_J=25^{\circ}\text{C}, I_{SD}=40\text{A}, V_{GS}=0\text{V}$		0.8	1	V
t_{rr}	Reverse Recovery Time ^(Note 1)	$T_J=25^{\circ}\text{C}, I_F=40\text{A}$ $di/dt=100\text{A}/\mu\text{s}$		95		nS
Q_{rr}	Reverse Recovery Charge ^(Note 1)			189		nC
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

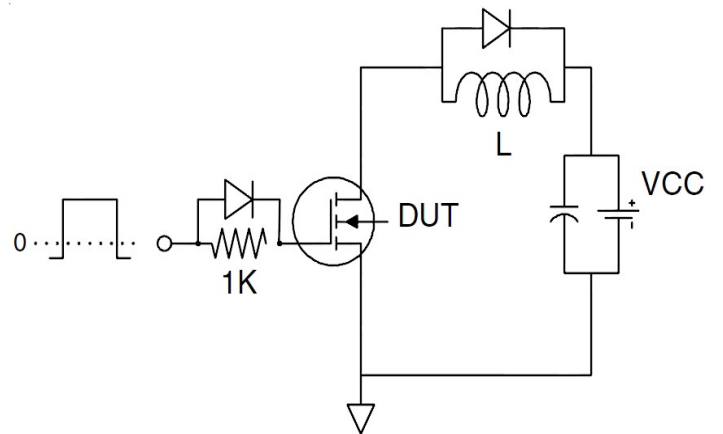
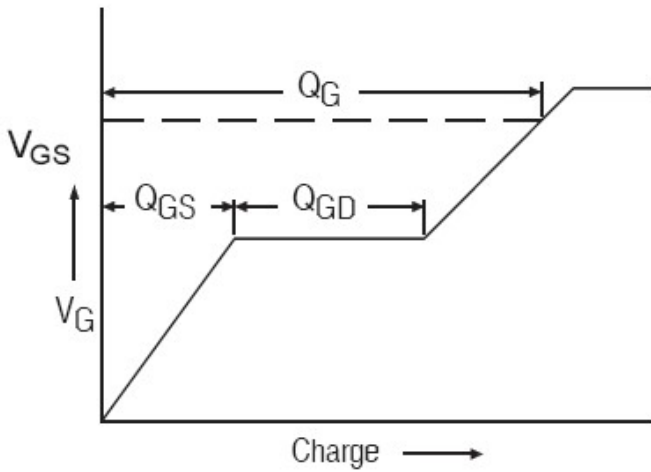
Notes 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$

Test Circuit

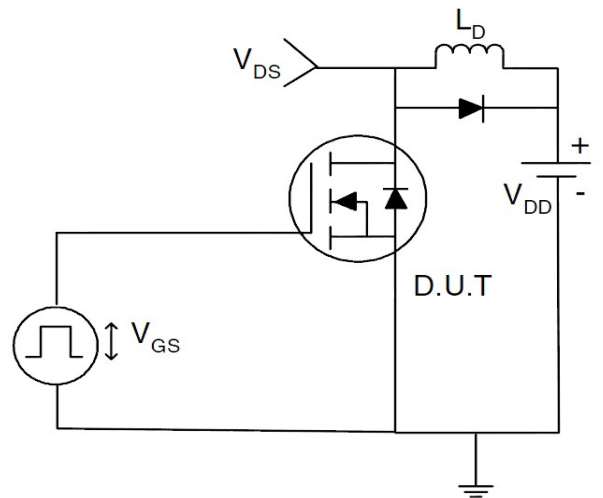
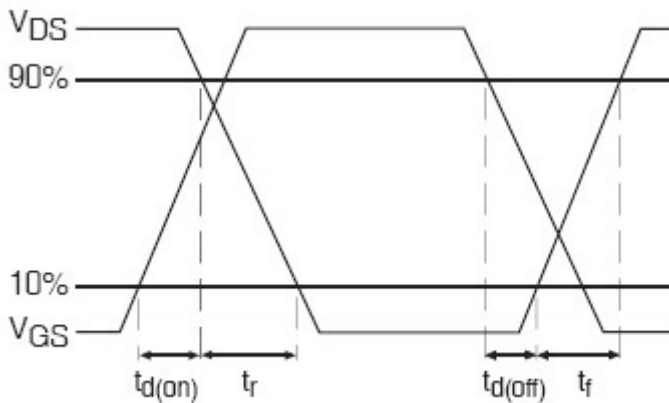
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Output Characteristics

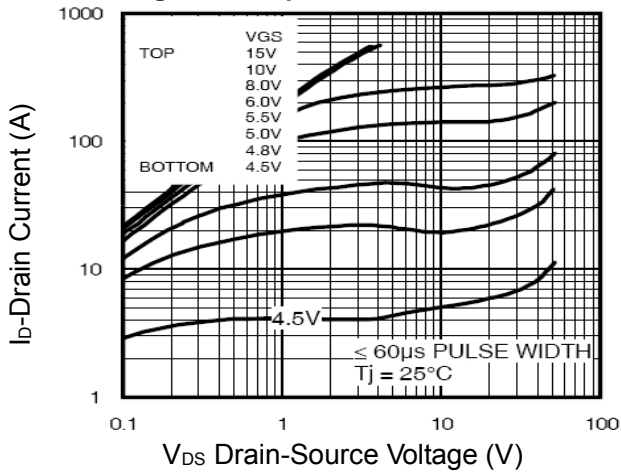


Figure2. Transfer Characteristics

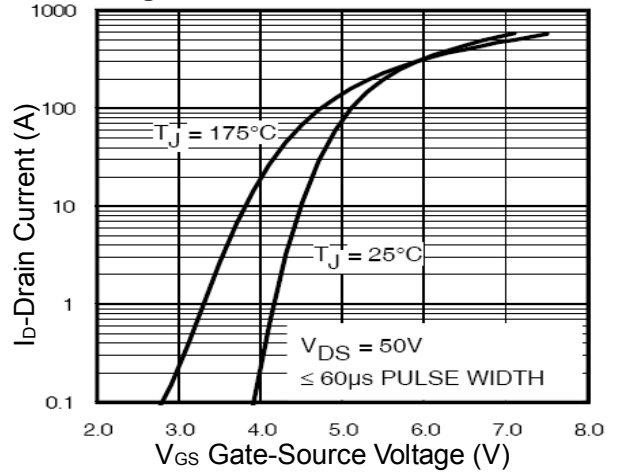


Figure3. $R_{DS(ON)}$ - Drain Current

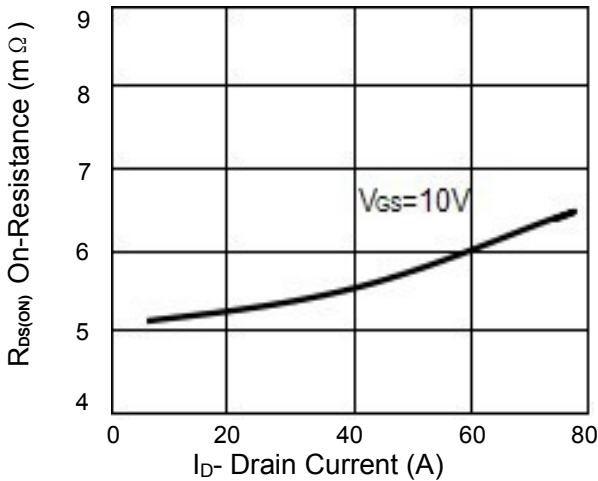


Figure4. $R_{DS(ON)}$ - Junction Temperature

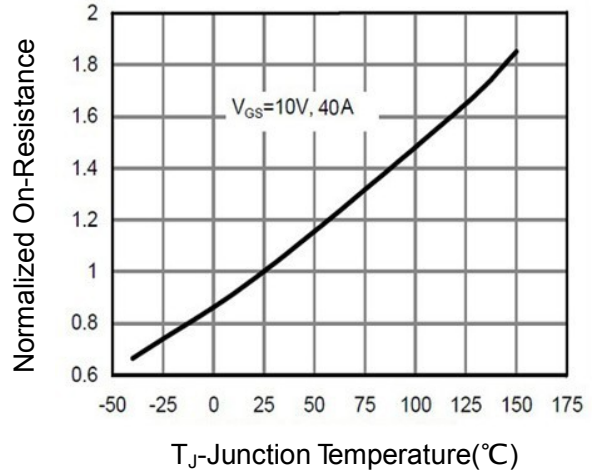


Figure5. Gate Charge

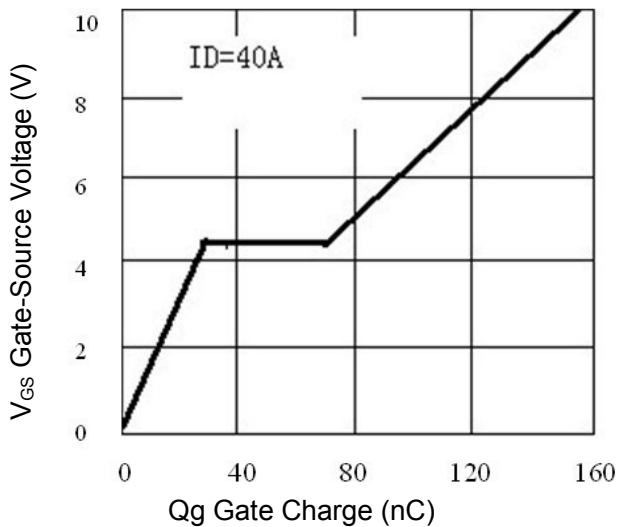


Figure6. Source- Drain Diode Forward

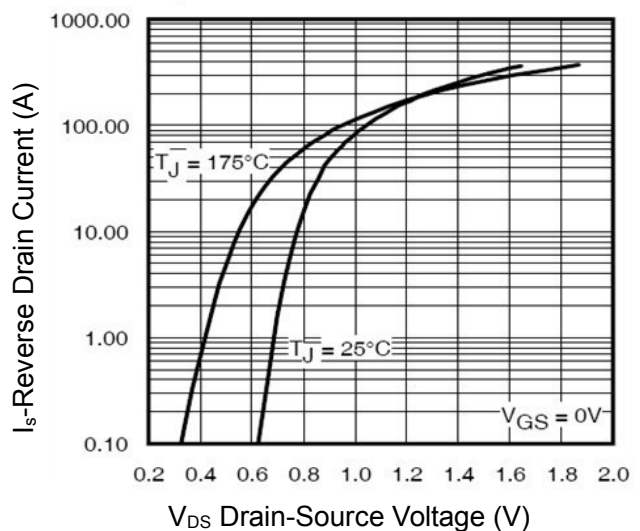


Figure7. Capacitance vs V_{DS}

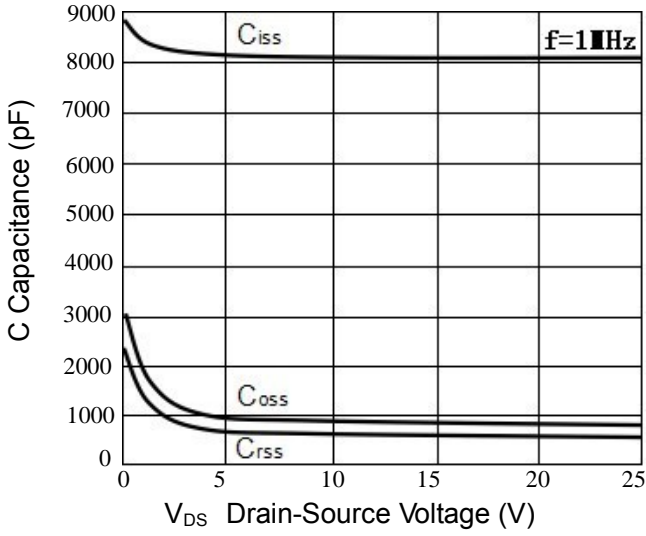


Figure8. Safe Operation Area

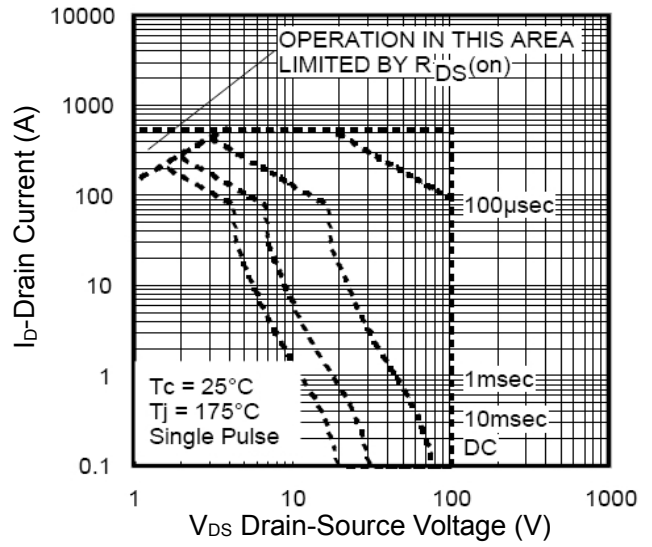


Figure9. BV_{DSS} vs Junction Temperature

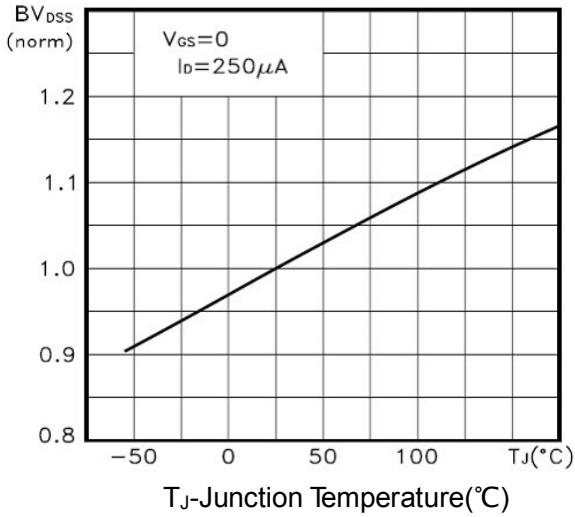


Figure10. V_{GS(th)} vs Junction Temperature

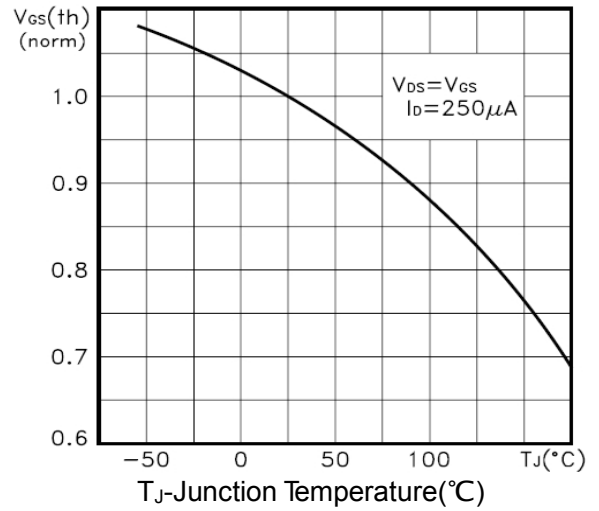
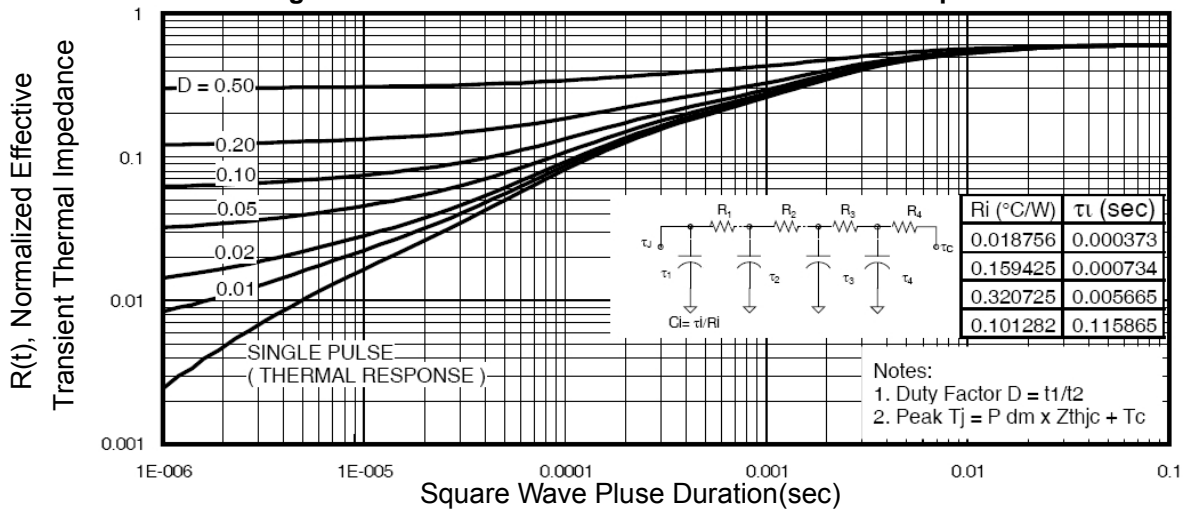
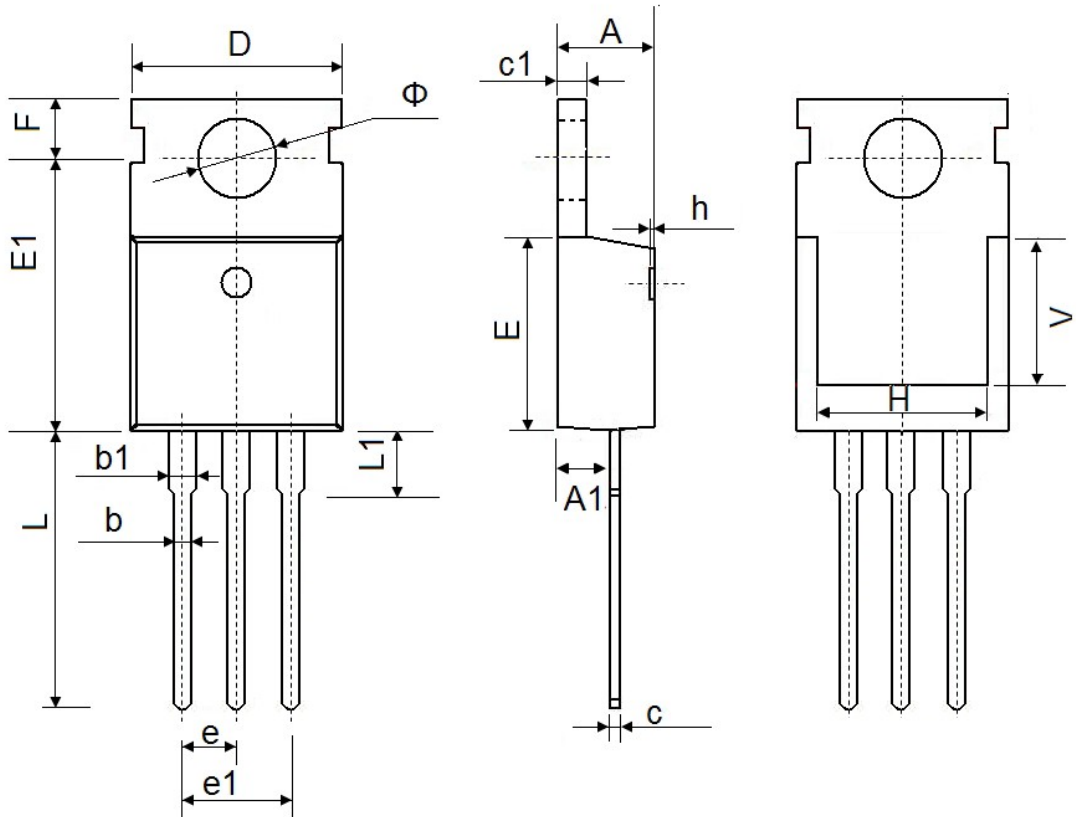


Figure11. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150